L	Hits	Search Text	DB	Time stamp
Number				2002/11/22
Į.	22	(US-6611002-\$ or US-6593191-\$ or US-5877070-\$ or US-6530991-\$ or US-6464780-\$ or US-6563118-\$).did. or (US-20020074552-\$ or US-20030011000-\$ or US-20030132433-\$ or US-20030102490-\$ or US-20020060317-\$).did. or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 10:41
-	14	(US-20020074552-\$ or DE-19802977-\$ or US-20030011000-\$).did. ((US-6611002-\$ or US-6593191-\$ or US-5877070-\$ or US-6530991-\$ or US-6464780-\$ or US-6563118-\$).did. or (US-20020074552-\$ or US-20030011000-\$ or US-20030132433-\$ or US-20030102490-\$ or US-20020060317-\$).did. or (US-20020074552-\$ or DE-19802977-\$ or	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 10:51
-	1	US-20030011000-\$).did.) and (GaN or AlGaN or (gallium near2 nitride\$1)) GaN/SiGe	USPAT; US-PGPUB;	2003/11/06 10:44
-	1	SiGe/GaN	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/06 10:44
-	50	SiGe near3 GaN	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 10:47
-	1521	(257/190-192).ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/06 10:50
-	8418	(257/79-103).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/11/06 10:50
_	1576	(257/13-19).ccls.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 10:50
_	10816	((257/190-192).ccls.) or ((257/79-103).ccls.) or ((257/13-19).ccls.)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 10:51
_	1298	(((257/190-192).ccls.) or ((257/79-103).ccls.) or ((257/13-19).ccls.)) and (GaN or AlGaN or (gallium near2 nitride\$1))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/06 10:51
_	159	(((((257/190-192).ccls.) or ((257/79-103).ccls.) or ((257/13-19).ccls.)) and (GaN or AlGaN or (gallium near2 nitride\$1))) and (SiGe or "SixGe(1-x)" or "Si.sub.x Ge.sub.(1-x)" or (silicon near germanium))	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/06 11:43

	1 11 1	/#2670212# #4242505# #4220020#	HCDAM	2002/11/06
-	114	("3670213" "4242595" "4289920"	USPAT	2003/11/06
		"4398342" "4424589" "4459325" "4482422" "4748485" "4756007"		11:38
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		"4772929" "4773063" "4841775"		
		"4845044" "4882300" "4901133"		
		"4984043" "4999842" "5051790"		
		"5055445" "5073981" "5081519"		
		"5140651" "5155658" "5185589"		
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		"5281834" "5310707" "5314547"		
		"5326721" "5352926" "5356509"		
		"5394489" "5406202" "5418389"		
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		"5473047" "5486406" "5491461"		
		"5492859" "5494711" "5504035"		
		"5504183" "5511238" "5515047"		
		"5515810" "5528057" "5528067"		
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		"5596205" "5602418" "5610744"	ĺ	
		"5650646" "5656382" "5659180"		
		"5674366" "5679965" "5731220"		
		, , , , , , , , , , , , , , , , , , , ,		
		"5754319" "5777350" "5789845" "5792679" "5801072" "5801105"		
		"5833603" "5863326" "5872493"		:
		"5874860" "5883564" "5907792"		
		"5912068" "5948161" "5959879"		
		"5987011" "6002375" "6011646"		
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		"6248459" "6252261" "6255198"		
		"6291319" "6139483" "6313486"		
		"6316785" "6316832" "6343171"		
		"2001/0013313").PN.		'
_	279	(GaN or AlGaN or (gallium near2	USPAT;	2003/11/17
		nitride\$1)) with (SiGe or "SixGe(1-x)" or	US-PGPUB;	11:54
		"Si.sub.x Ge.sub.(1-x)" or (silicon near	EPO; JPO;	
		germanium))	DERWENT;	
		, s	IBM TDB	
_	57	Watanabe near Daisuke	USPAT;	2003/11/06
		Wasanabe near barbane	US-PGPUB;	11:44
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
_	2	(Watanabe near Daisuke) and (GaN or AlGaN	USPAT;	2003/11/06
-	2	or (gallium near2 nitride\$1))	US-PGPUB;	11:46
		or (dariimm mears micridesi))		11.70
			EPO; JPO;	
			DERWENT;	
	_	#2002022011#	IBM_TDB	2003/11/06
-	4	"2003023011"	USPAT;	2003/11/06
			US-PGPUB;	11:46
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	"2003JP-023011"	USPAT;	2003/11/06
			US-PGPUB;	11:46
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	2003JP-023011\$3	USPAT;	2003/11/06
			US-PGPUB;	11:47
	!		EPO; JPO;	
			DERWENT;	
			IBM TDB	
	L			!

		D0027D02201142	TICDAG	1 0000 (11 /05
-	0	2003JP023011\$3	USPAT; US-PGPUB;	2003/11/06
			EPO; JPO;	11:4/
			DERWENT;	
			IBM TDB	
_	1	JP2003023011\$3	USPAT;	2003/11/06
!	*	01200302301143	US-PGPUB;	11:48
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	2001-204216	USPAT;	2003/11/06
			US-PGPUB;	11:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	2	"2001204216"	USPAT;	2003/11/06
			US-PGPUB;	11:49
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000/05/55
-	2	JP2001204216\$2	USPAT;	2003/11/06
i .			US-PGPUB;	11:49
			EPO; JPO;	
			DERWENT;	
	177	(Can on AlCan on (gallium near)	IBM_TDB USPAT;	2002/11/06
-	1/	(GaN or AlGaN or (gallium near2 nitride\$1)) and ((SiGe or "SixGe(1-x)"	USPAT; US-PGPUB;	2003/11/06
		or "Si.sub.x Ge.sub.(1-x)" or (silicon	EPO; JPO;	12:4/
		near germanium)) near3 (buffer or graded	DERWENT;	
		or intermediate))	IBM TDB	
_	2	"20030102490"	USPAT;	2003/11/06
			US-PGPUB;	12:08
			EPO; JPO;	· · ·
			DERWENT;	
			IBM TDB	
-	9	("Re33693" "4861393" "4994866"	USPĀT	2003/11/06
		"5019882" "5155571" "5442205"		12:41
		"5461243" "5683934" "5705421").PN.		
_	1	(USPAT;	2003/11/06
		or AlGaN or (gallium near2 nitride\$1)))	US-PGPUB;	12:49
		and ((SiGe or "SixGe(1-x)" or "Si.sub.x	EPO; JPO;	
		Ge.sub.(1-x)" or (silicon near	DERWENT;	
		germanium)) near3 (buffer or graded or	IBM_TDB	
	112	intermediate))	IICDAM -	2002/11/06
_	113		USPAT; US-PGPUB;	2003/11/06
		or AlGaN or (gallium near2 nitride\$1))) and ((SiGe or "SixGe(1-x)" or "Si.sub.x	EPO; JPO;	12:43
		Ge.sub.(1-x)" or (silicon near	DERWENT;	
		germanium)))	IBM TDB	
_		"2003JP-023011" and ((SiGe or	USPAT;	2003/11/06
		"SixGe(1-x)" or "Si.sub.x Ge.sub.(1-x)"	US-PGPUB;	12:51
		or (silicon near germanium)) with	EPO; JPO;	
		substrate)	DERWENT;	
		·	IBM_TDB	
-	[0	"2003JP-023011" and ((silicon near	USPAT;	2003/11/06
		germanium) with substrate)	US-PGPUB;	12:51
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0		USPAT;	2003/11/06
		germanium) with substrate)	US-PGPUB;	12:51
			EPO; JPO;]
			DERWENT;]
	1		IBM TDB	1

"SixGe(1-x)" or "Si.sub.x Ge.sub.(1-x)" or (silicon near germanium) with substrate) (or (silicon near germanium) with substrate) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or Silicon with germanium with substrate) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or Silicon with germanium with substrate) and epitax85 percent spreeze property; IBM TOB (solid) (or AlGaN or (gallium near2 (solid) (or AlGaN o		39	<pre>and ((SiGe or "SixGe(1-x)" or "Si.sub.x Ge.sub.(1-x)" or (silicon near</pre>	EPO; JPO; DERWENT;	2003/11/06 12:52
			"SixGe(1-x)" or "Si.sub.x Ge.sub.(1-x)" or (silicon near germanium)) with substrate)	IBM_TDB	
- 4 "2003023011"	-	7	(GaN or AlGaN or (gallium near2 nitride\$1)) with (crack near2 level)	US-PGPUB; EPO; JPO; DERWENT;	
Can be near Daisuke and ((gallium USPĀT; US-PCPUB; EPO; JPO; DERWENT; IBM TDB LINE TIBM TDB LINE LIN	-	4	"2003023011"	USPAT; US-PGPUB; EPO; JPO; DERWENT;	' '
CANABE near MITSURU) and ((gallium near2	_	2		USPAT; US-PGPUB; EPO; JPO; DERWENT;	1
- 59 (Watanabe near Daisuke) Spate Spate	-	2		USPAT; US-PGPUB; EPO; JPO; DERWENT;	
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EEO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EEO; JPO; DERWENT; IBM TDB USPAT "5639187" "56394887" "5621227" "5659187" "5728623" "6010937" "6030884" "603983" "6017560" "6191006" "6252221" "6392257").PN.	-	59	(Watanabe near Daisuke)	USPAT; US-PGPUB; EPO; JPO; DERWENT;	1 ' '
US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	-	119	shouxiang near hu	US-PGPUB; EPO; JPO; DERWENT;	1
- 16 ("4863877" "5091767" "5134446" USPĀT 2003/11/17	-	2	"6589335"	US-PGPUB; EPO; JPO; DERWENT;	1
- 44 (GaN or AlGaN or (gallium near2 nitride\$1)) with buffer with (thermal near expan\$6) - 104 (GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate - 48 ((GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate) - 48 ((GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate) - 48 ((GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate) and epitax\$5 - 11 ((GaN or AlGaN or (gallium near2 USPĀT; IBM_TDB		16	"5221413" "5408487" "5621227" "5659187" "5728623" "5751753" "6010937" "6030884" "6039803" "6057560" "6191006" "6252221"		11:44
- 44 (GaN or AlGaN or (gallium near2 nitride\$1)) with buffer with (thermal near expan\$6) - 104 (GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate - 48 ((GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate) and epitax\$5 - 48 ((GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate) and epitax\$5 - 11 ((GaN or AlGaN or (gallium near2 Normanium with substrate)) and epitax\$5 - 11 ((GaN or AlGaN or (gallium near2 Normanium with substrate)) and epitax\$5 - 11 ((GaN or AlGaN or (gallium near2 Normanium with substrate)) and epitax\$5	-	0	6589335.URPN.	USPAT	1
- 104 (GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate - 48 ((GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate) and epitax\$5 - 11 ((GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate) and epitax\$5 - 11 ((GaN or AlGaN or (gallium near2 USPĀT; 14:33	_	44	nitride\$1)) with buffer with (thermal	US-PGPUB; EPO; JPO; DERWENT;	2003/11/17
- 48 ((GaN or AlGaN or (gallium near2 nitride\$1)) with silicon with germanium with substrate) and epitax\$5 EPO; JPO; DERWENT; IBM_TDB USPAT; 2003/11/17	_	104	nitride\$1)) with silicon with germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT;	
- 11 ((GaN or AlGaN or (gallium near2 USPAT; 2003/11/17	-	48	nitride\$1)) with silicon with germanium	USPĀT; US-PGPUB; EPO; JPO; DERWENT;	· ·
or "SixGe(1-x)" or "Si.sub.x EPO; JPO; Ge.sub.(1-x)" or (silicon near DERWENT; germanium))	_	11	<pre>nitride\$1)) near2 substrate) same (SiGe or "SixGe(1-x)" or "Si.sub.x Ge.sub.(1-x)" or (silicon near</pre>	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2003/11/17 16:26

-	1	WO98/44569	USPAT;	2003/11/17
			US-PGPUB;	16:27
			EPO; JPO;	
			DERWENT;	l
			IBM_TDB]
-	0	WO9844569	USPAT;	2003/11/17
			US-PGPUB;	16:27
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	i
-	2	WO adj "9844569"	USPAT;	2003/11/17
			US-PGPUB;	16:27
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	